20V P-Channel Enhancement Mode MOSFET

Description

The NP2301FVR-J uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 1.8V. This device is suitable for use as a load switch or in PWM applications.

General Features

V_{DS} =-20V I_D =-2.1A

$R_{DS(ON)}$(Typ.)=178 mΩ @V_{GS}=-2.5V

$R_{DS(ON)}$(Typ.)=138 mΩ @V_{GS}=-4.5V

High power and current handing capability

Lead free product is acquired

Surface mount package

Application

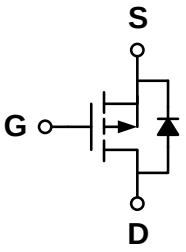
PWM applications

Load switch

Package

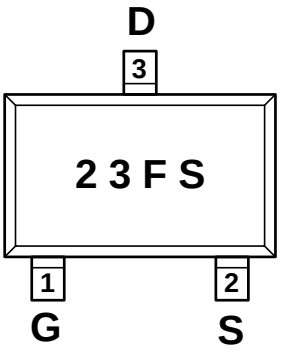
SOT-23

Schematic diagram



Marking and pin assignment

SOT-23
(TOP VIEW)



Ordering Information

Part Number

Electrical Characteristics (TA=25 unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ

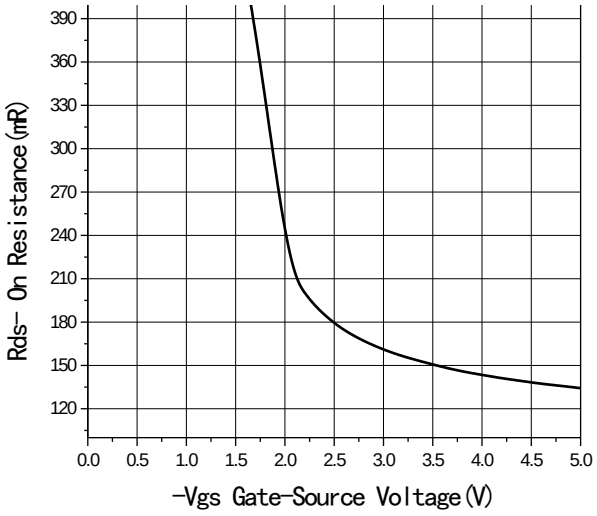


Fig7 Rdson-Gate Drain voltage

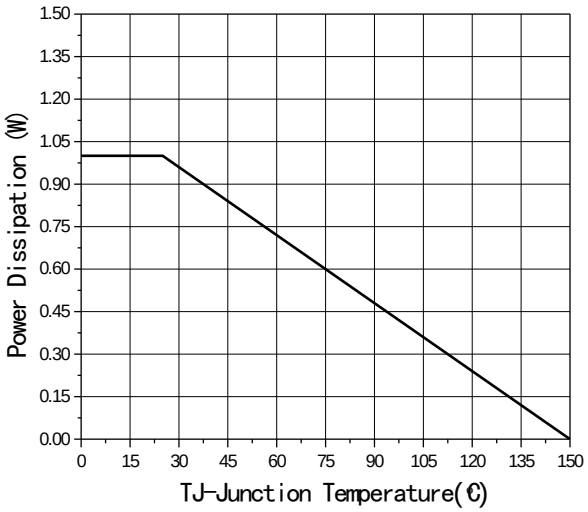


Fig8 Power De-rating